

# Nanoscale thermal characterization and solid-state heat management

**Miguel Muñoz Rojo**

**UNIVERSITY  
OF TWENTE.**

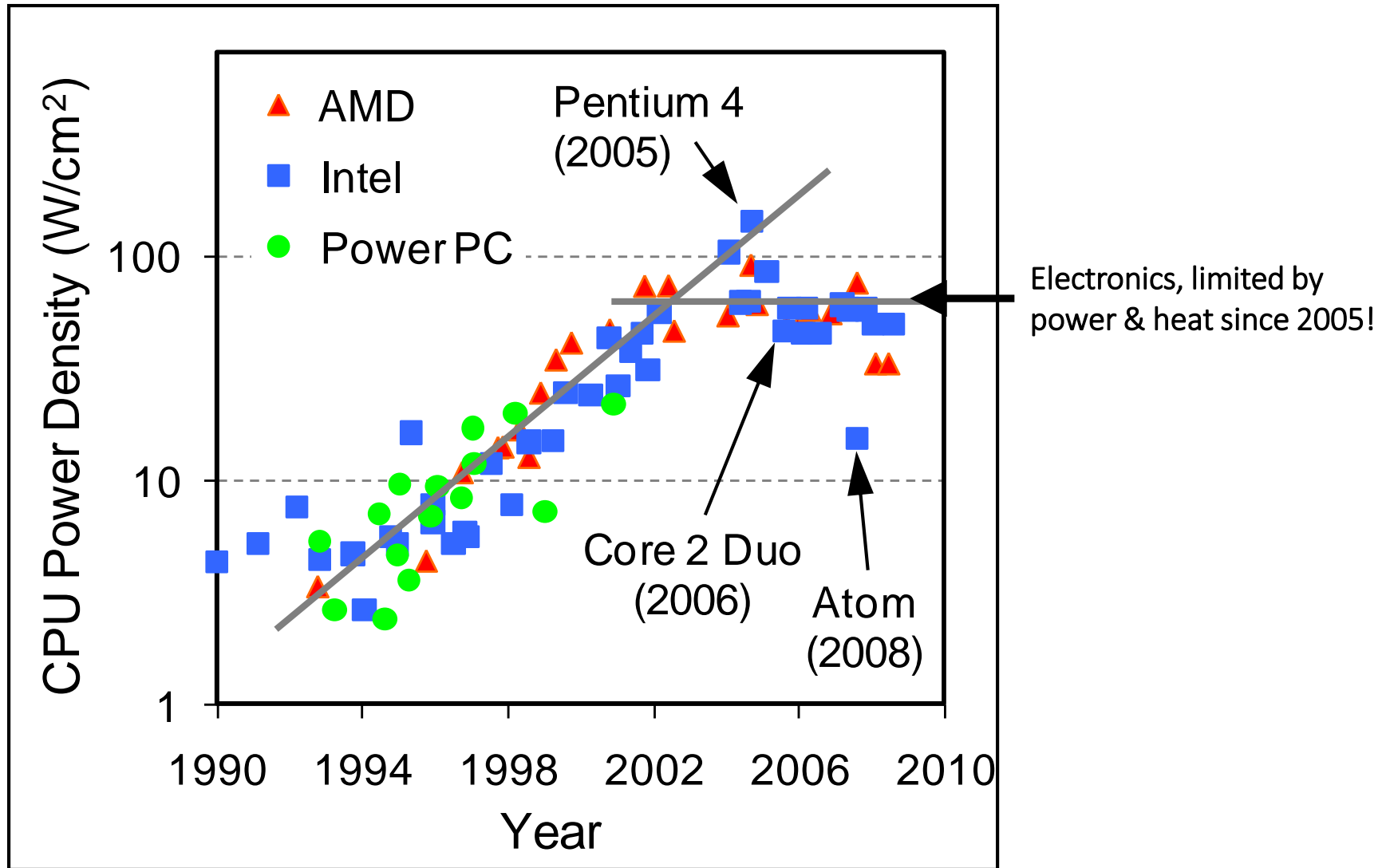
*Científico Titular<sup>1</sup> & Associate Prof.<sup>2</sup>*  
*<sup>1</sup>National Research Council of Spain, ICMM, CSIC*  
*<sup>2</sup>University of Twente, the Netherlands*

*ESMolNa, Santa Pola, 20<sup>th</sup> May 2025*



European Research Council  
Established by the European Commission

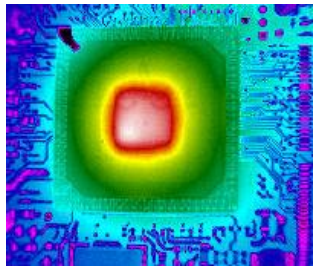
# Motivation



\* E. Pop, Nano Research, 3, 147-169 (2010)

# Heat dissipation in electronics

Devices

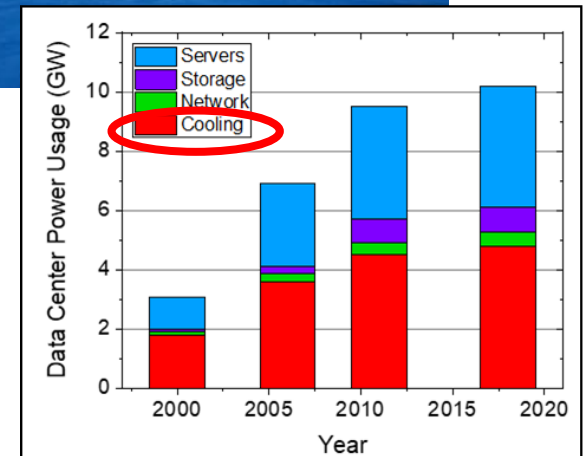
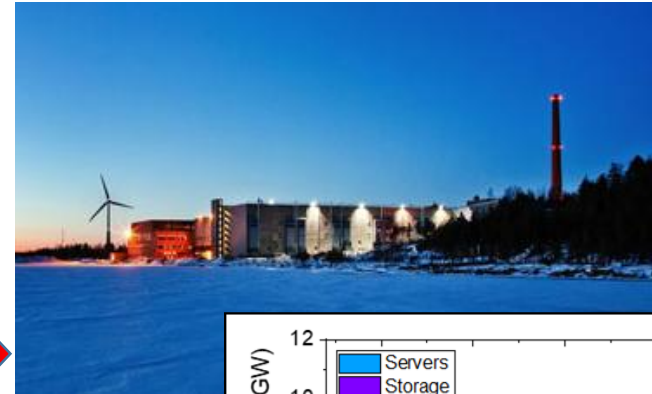


Wasted heat



<http://www.phys.ncku.edu.tw/~htsu/humor/fry-egg.html>

Data centers

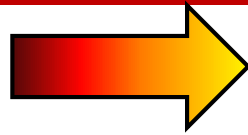
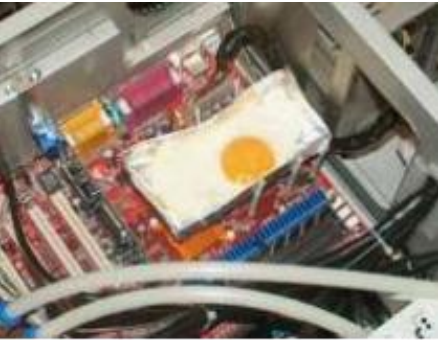


\* E. Pop, Nano Research, 3, 147-169 (2010)

- Gaining thermal insights of our electronic devices and learn how to manage this heat is an essential aspect to our electrified future

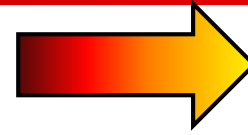
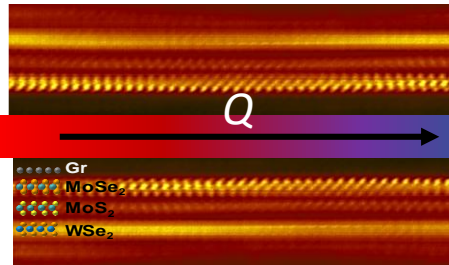
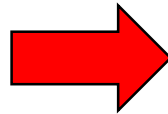
# My research line: Nano- to macro- approach

Energy dissipation



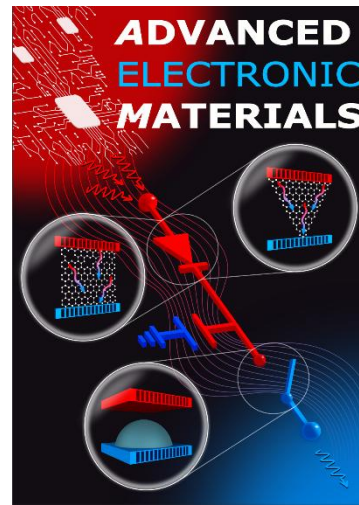
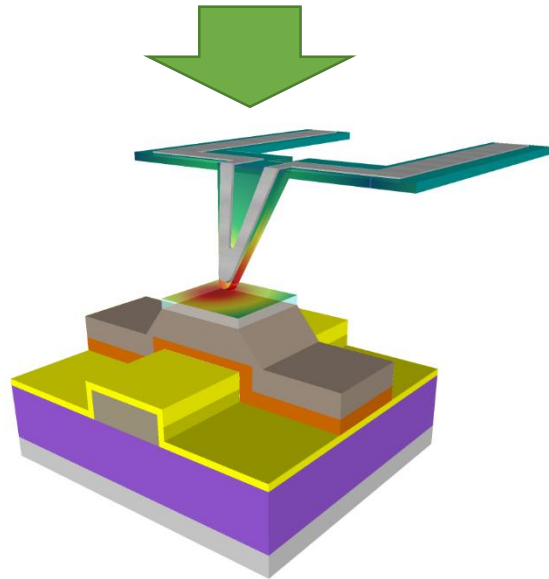
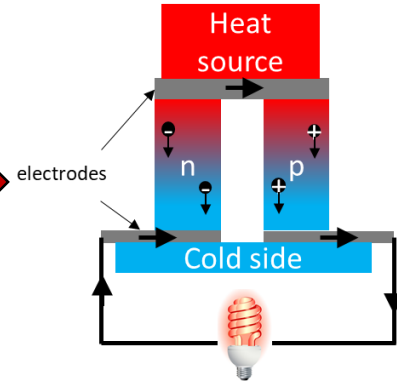
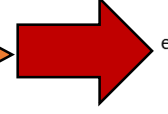
Energy management

Heat



Energy harvesting

Heat

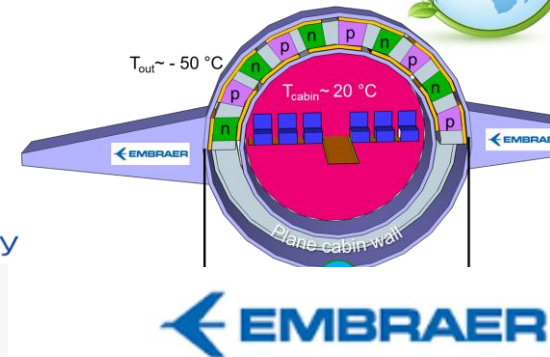


THALES



InnoEnergy

ASML



- Nanoscale thermometry

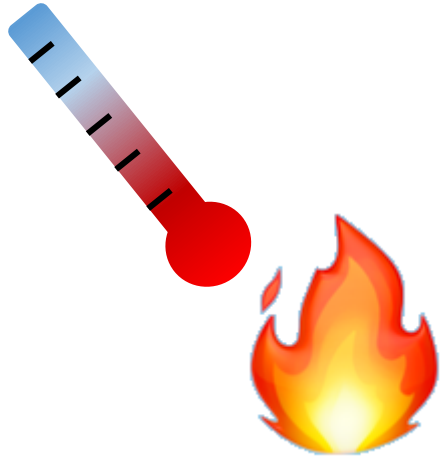
- Routing heat
- Active heat control

- Thermoelectrics

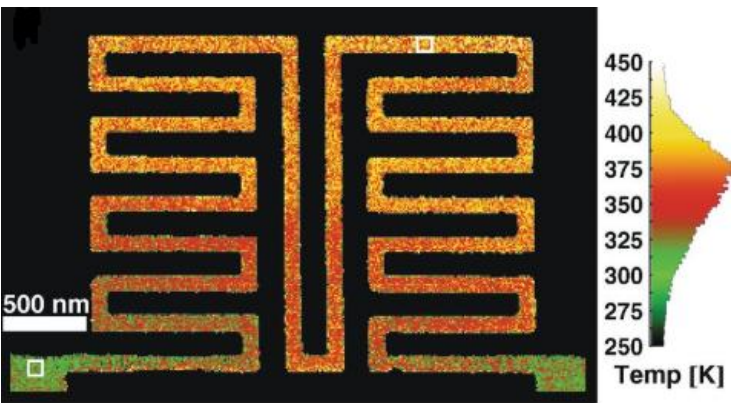
# Advanced thermal characterization

# How Can We Measure Temperature at Nanoscale?

## Thermometer

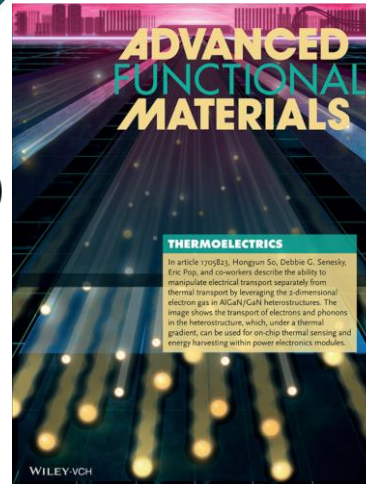
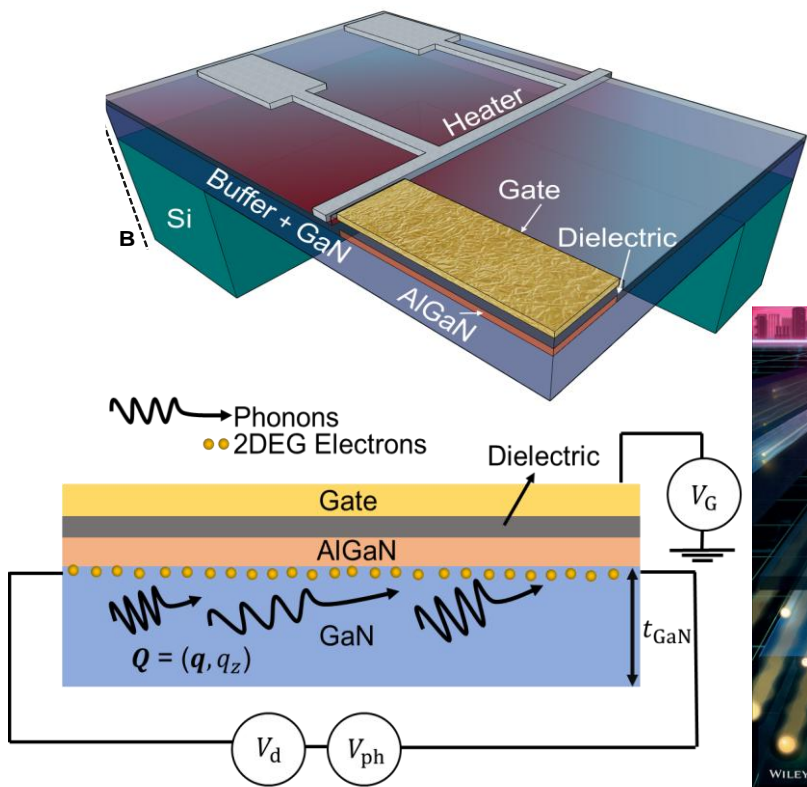


Need for other approaches in the nano- and micro-scale...



M. Mecklenburg, *et al.*, *Science*, 347, 6222, 2015

## Electro-thermal methods



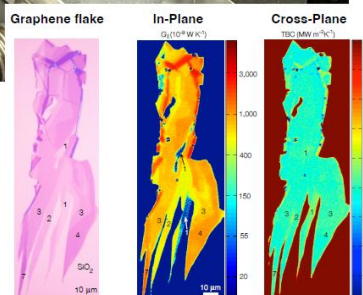
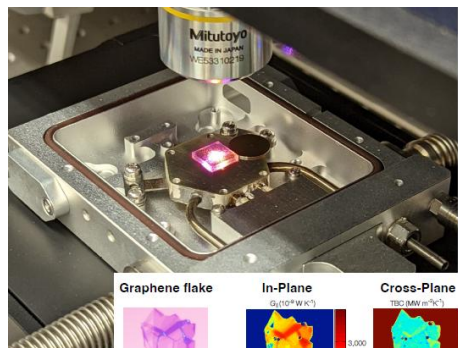
**No thermal maps**

A.Yalamarthy, **M. Muñoz Rojo**, [...] *et al.*, *Nano Letters* (2019)

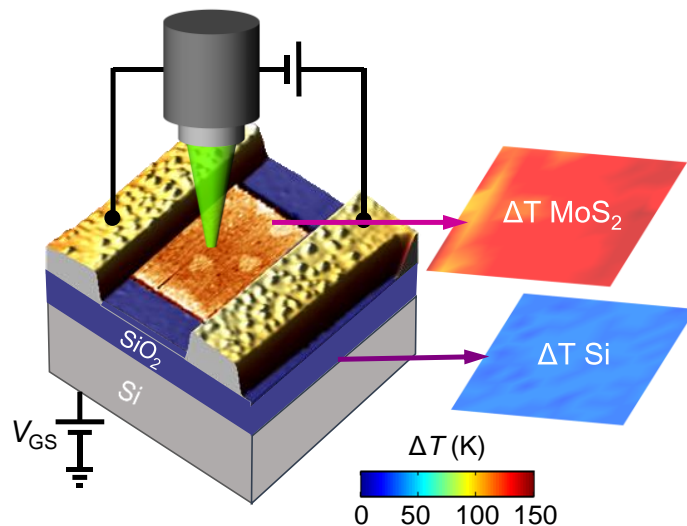
AS Yalamarthy, H So, **M Muñoz Rojo**, [...], E. Pop and DG Senesky, *Advanced Functional Materials* 28 (22), 1705823, 2018

# Spatially Resolved Device Thermometry

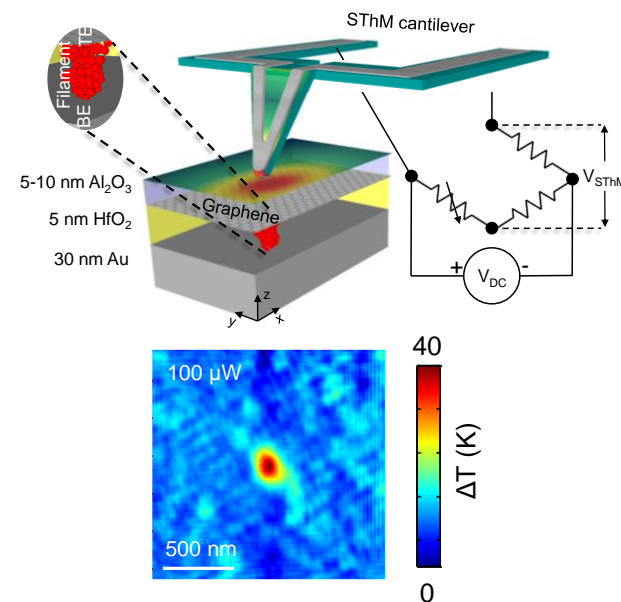
## FDTR



## Raman



## SThM (AFM)



+ Unique SThM calibration approach

~ 2-3  $\mu$ m

~ 0.5  $\mu$ m

~ 0.05  $\mu$ m

**Medium-scale  
T-maps**

**Material  
selectivity**

**High spatial  
resolution**

E. Tornero, [...], **M. Muñoz Rojo**, *Submitted* (2025)

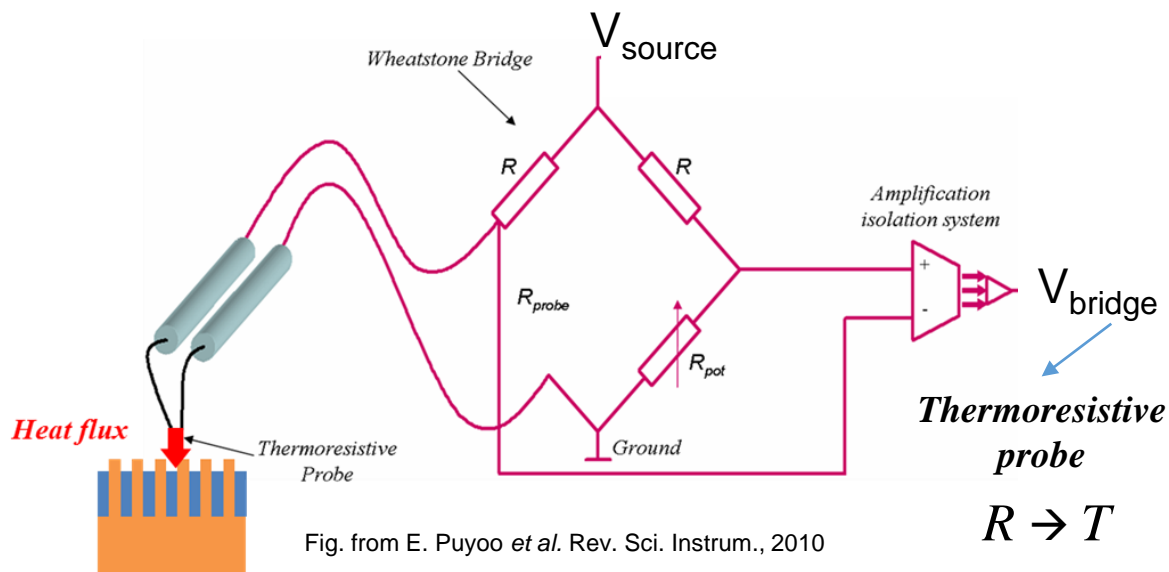
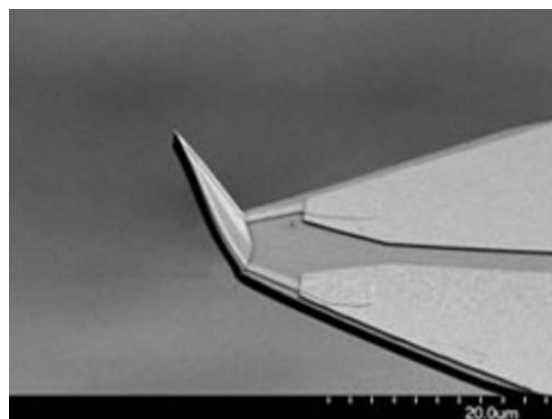
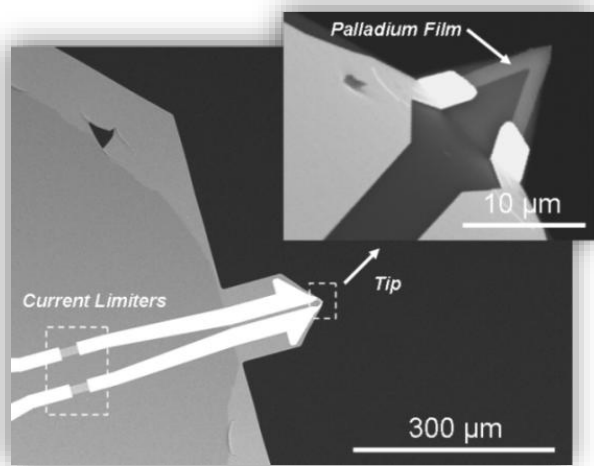
E. Yalon,..., **M. Muñoz Rojo**,... *et al.*, *Nano Lett.* 17, 3429 (2017)

S. Deschmuk\*, **M. Muñoz Rojo**\*, *et al.*, *Science Adv.* (2022)

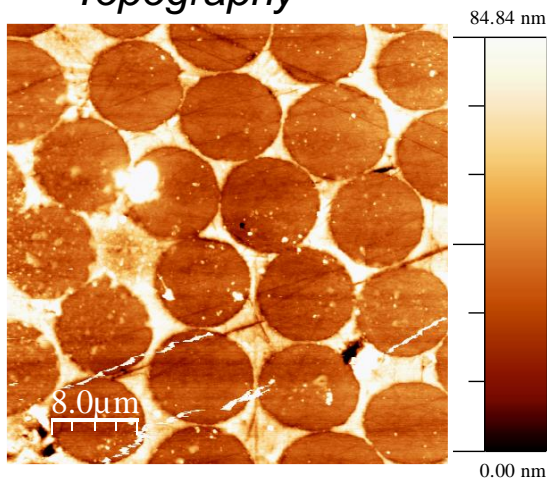
\*Authors contributed equally as first author

# SThM thermal mapping

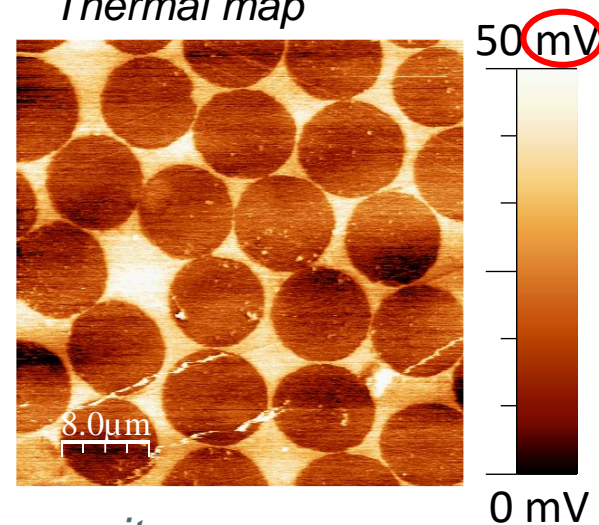
## Thermal Probes: Pd/SiN probe



## Topography



## Thermal map

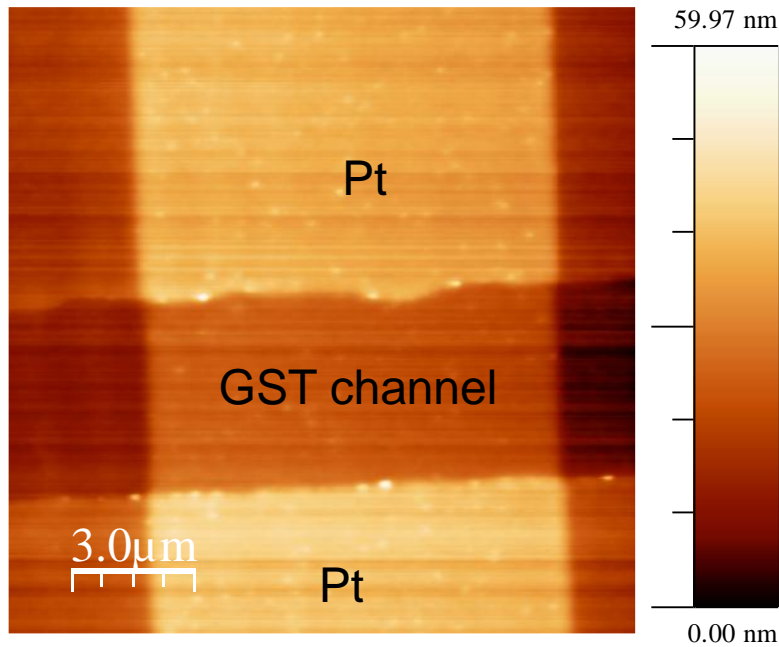


carbon fiber – epoxy composite (\*Anasys Instruments)

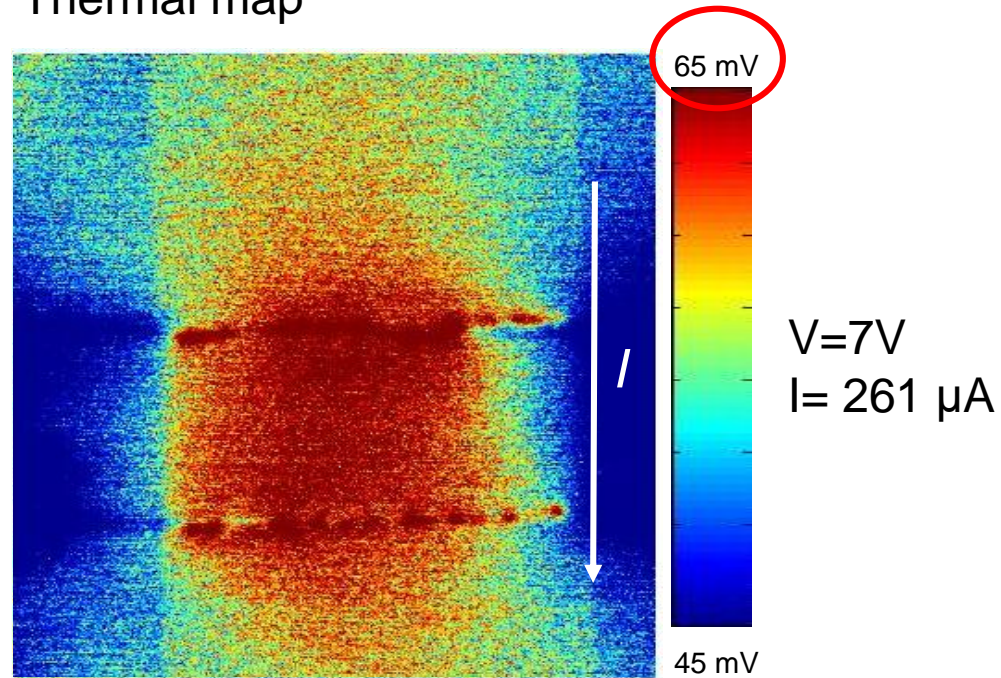
# Thermal mapping of self-heating GST device

- $\text{Ge}_2\text{Sb}_2\text{Te}_5$  (GST) device

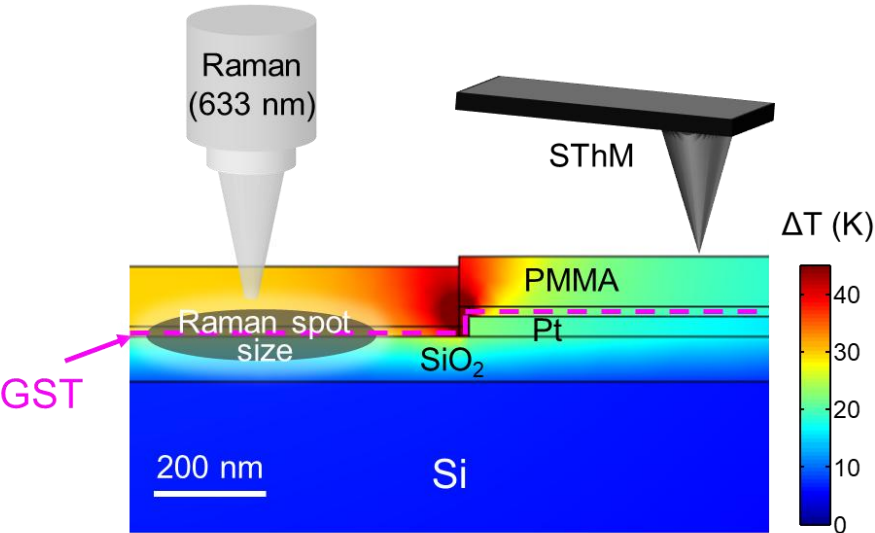
Topography



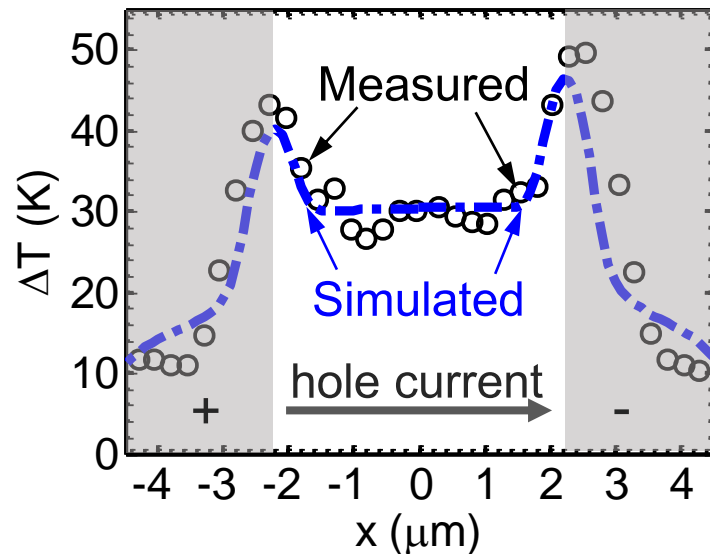
Thermal map



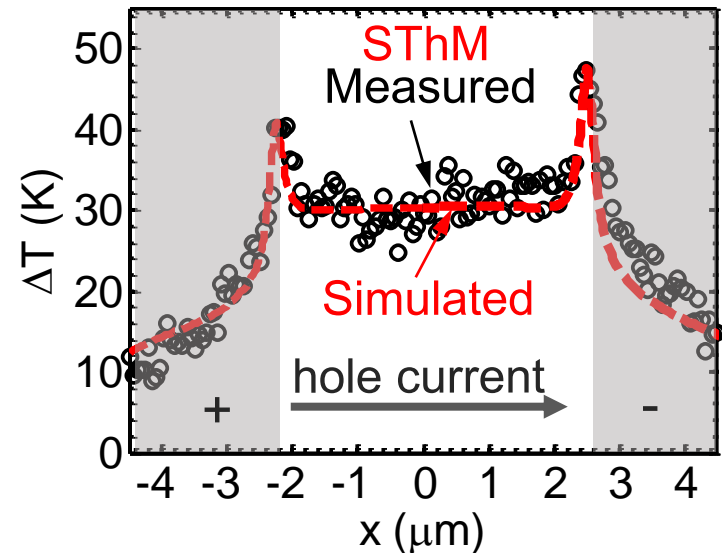
# Sensing mode: Temperature calibrated with Raman



Raman



**Significant heating at contacts**



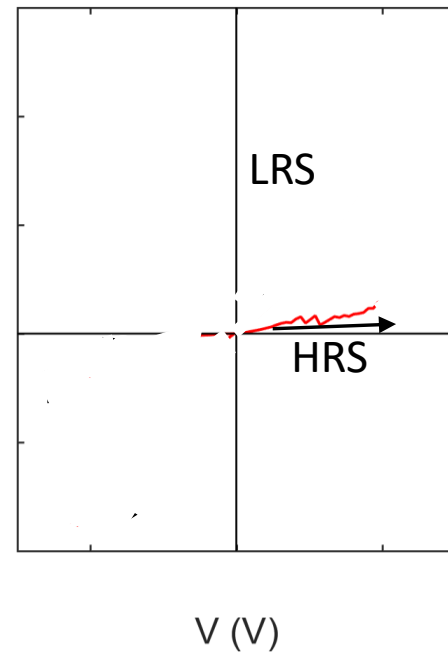
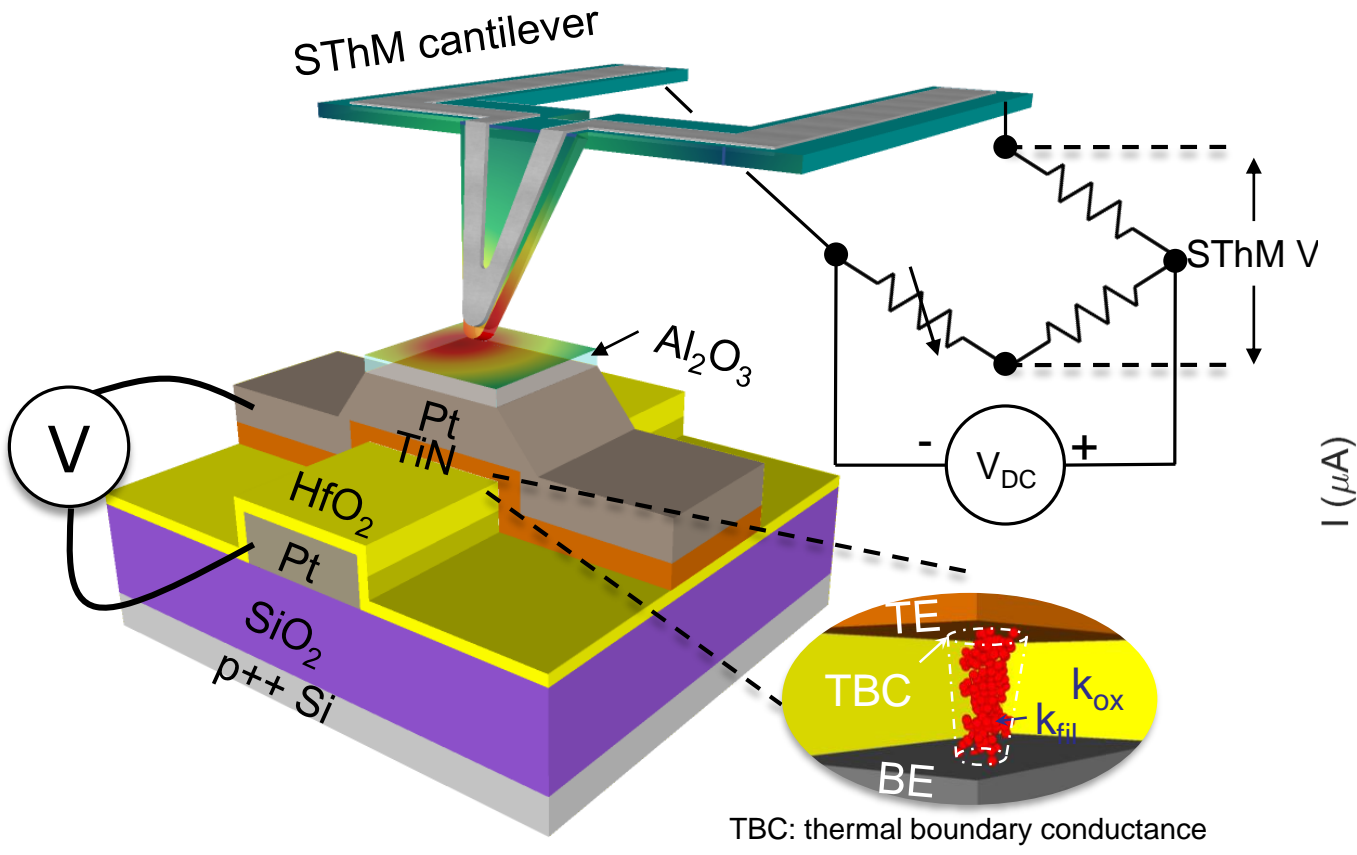
Thermal properties (simulation):

$$\text{TBC}_{\text{GST/SiO}_2} = 50 \text{ MW/m}^2/\text{K}$$

$$\text{TBC}_{\text{GST/Pt}} = 100 \text{ MW/m}^2/\text{K}$$

GST thermopower = 450  $\mu\text{V}/\text{K}$  (lumped thermoelectric with thermionic effect)

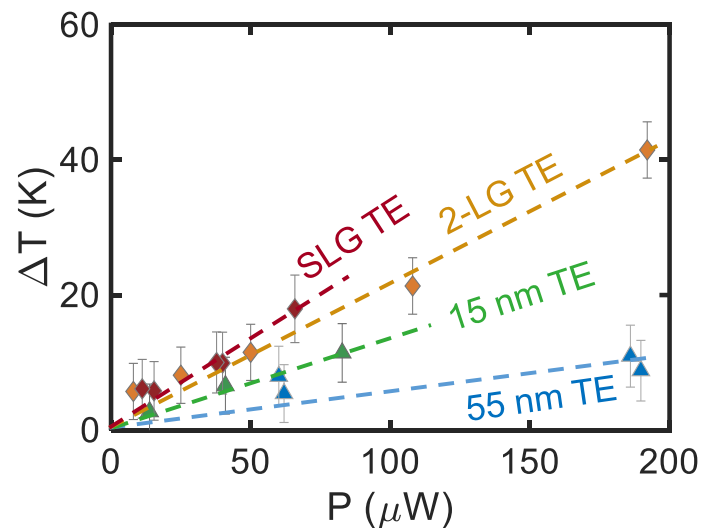
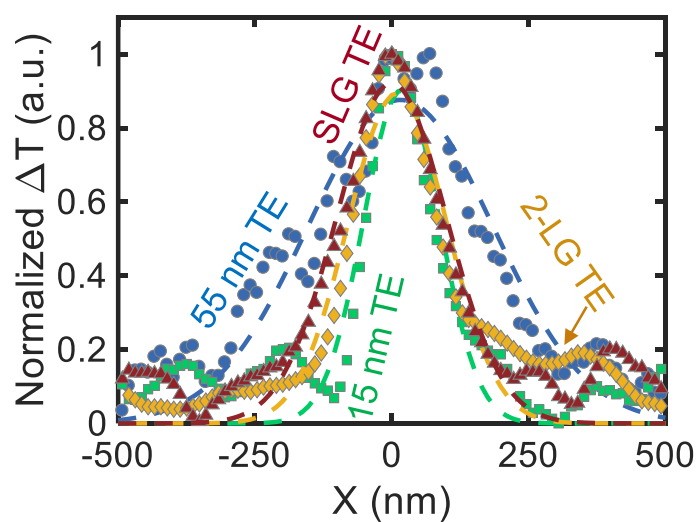
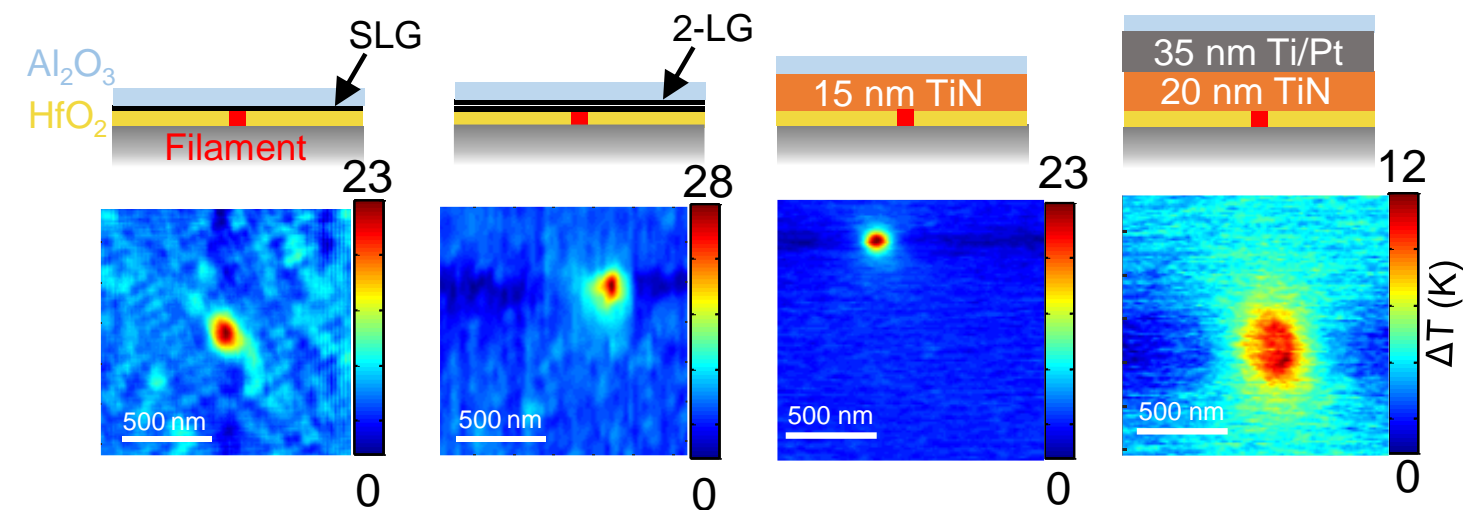
# SThM on RRAM Devices



- $\text{HfO}_2$  RRAM devices with filaments self-heat because of external bias ( $V$ )

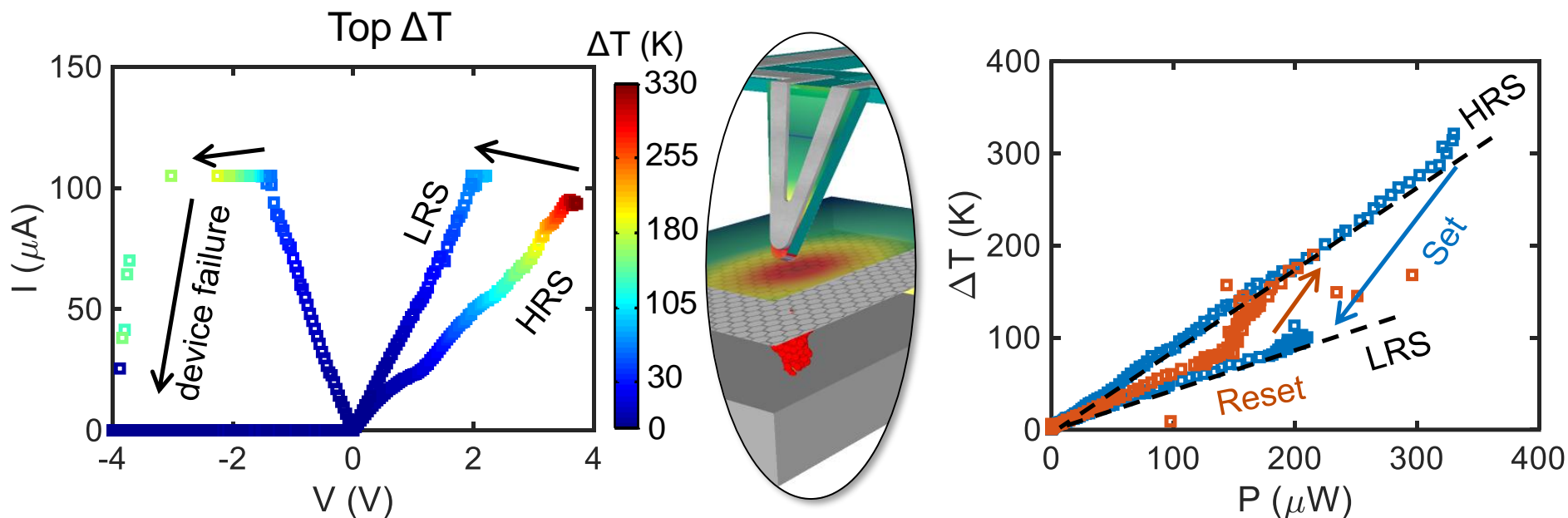
S. Deshmukh\*, M. Muñoz Rojo\*, ..., E. Pop, *Science Adv.*, 2022

# Comparing Hot Spots Across Devices



- Top temperatures are comparable across different TE thickness

# In operando SThM – Graphene as TE

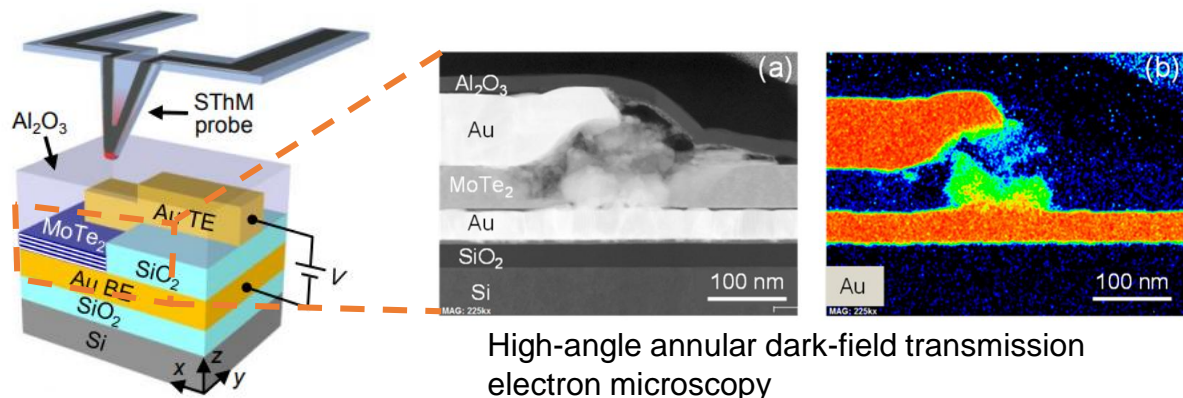


- Switching  $\Delta T_{\text{fil}} > \Delta T_{\text{top}} > 300$  K above room temperature (RT).
- Dependence of top  $\Delta T$  on power changes reversibly with switching
- Device failure (eventual hard reset) at relatively low  $\Delta T$ .

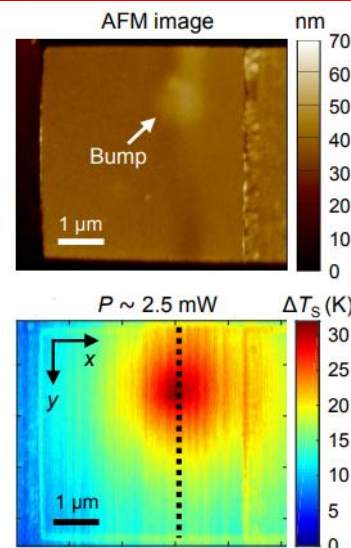
S. Deshmukh\*, M. Muñoz Rojo\*, ..., E. Pop, *Science Adv.*, 2022

# Thermal mapping extended to other devices

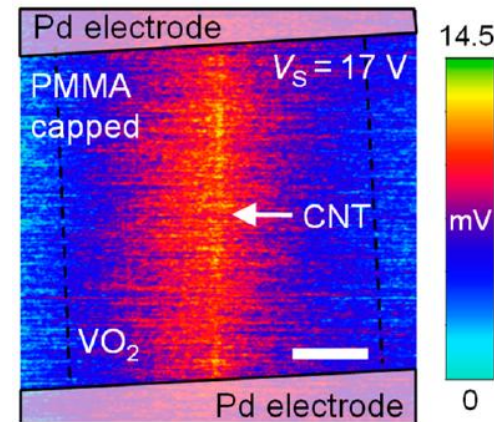
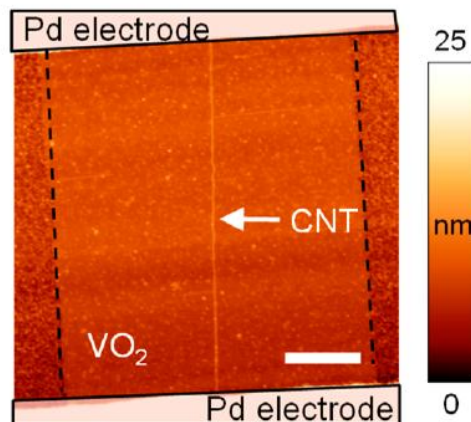
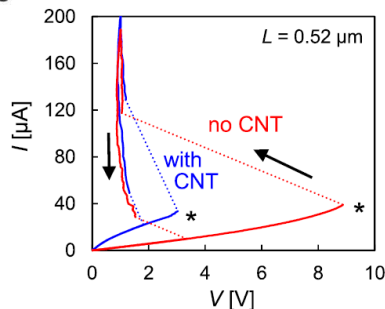
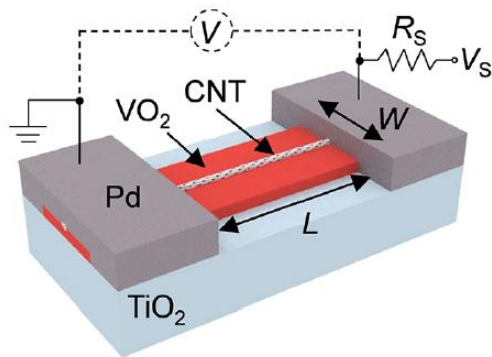
- CB-RAMs based on 2D materials



High-angle annular dark-field transmission electron microscopy  
I. Datye, M. Muñoz Rojo, [...], E. Pop, *Nano Letters*, 2020



- VO<sub>2</sub> phase change triggered by CNTs

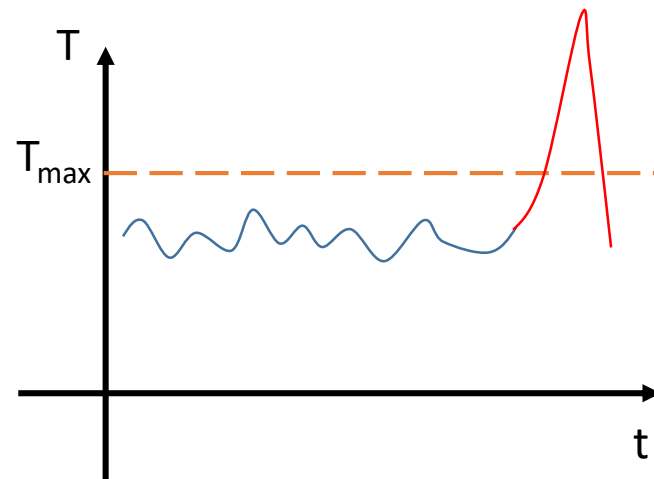
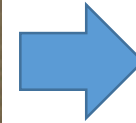
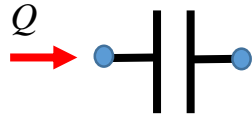


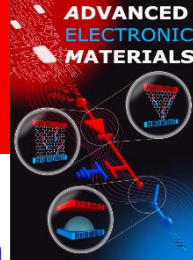
S. Bohachuck, M. Muñoz Rojo, [...], E. Pop, *Nano Letters*, 2020

# Solid-state thermal management

# Thermal mismanagement of electronics and beyond...

Nowadays limited by thermal resistors & capacitors

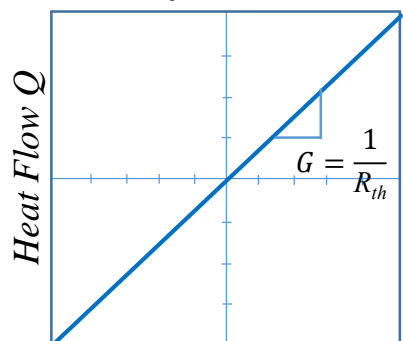




## Passive thermal device



**Transfer Function:  
Symmetric**



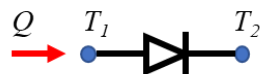
Thermal Bias:  $\Delta T = T_1 - T_2$   
( $T_{avg}$  fixed)

$$\Delta T = Q \times R_{th}$$

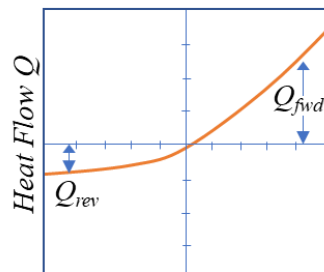
$$R_{th} = \frac{1}{k} \cdot \frac{L}{A}$$

## Active thermal devices

### a) Diode

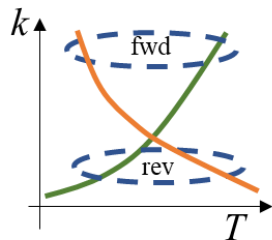


**Transfer Function:  
Asymmetric**



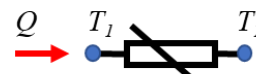
Thermal Bias:  $\Delta T = T_1 - T_2$   
( $T_{avg}$  fixed)

Example

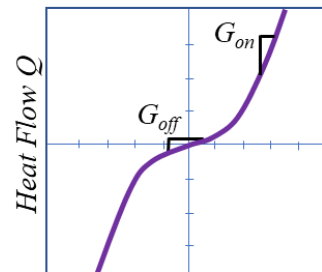


C. Dames, *J. Heat Transfer*, 131, 061301 (2009)

### b) Regulator

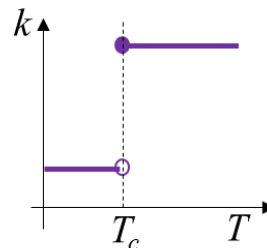
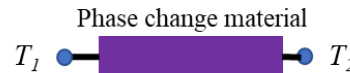


**Transfer Function:  
Nonlinear**



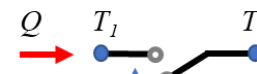
Thermal Bias:  $\Delta T = T_1 - T_2$   
( $T_{avg}$  fixed)

Example

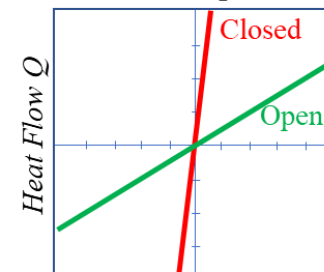


Xie et al., *Adv. Funct. Mater.*, 21, 1602 (2011)

### c) Switch

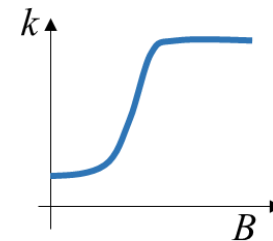
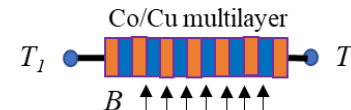


**Transfer Function:  
Control dependent**



Thermal Bias:  $\Delta T = T_1 - T_2$   
( $T_{avg}$  fixed)

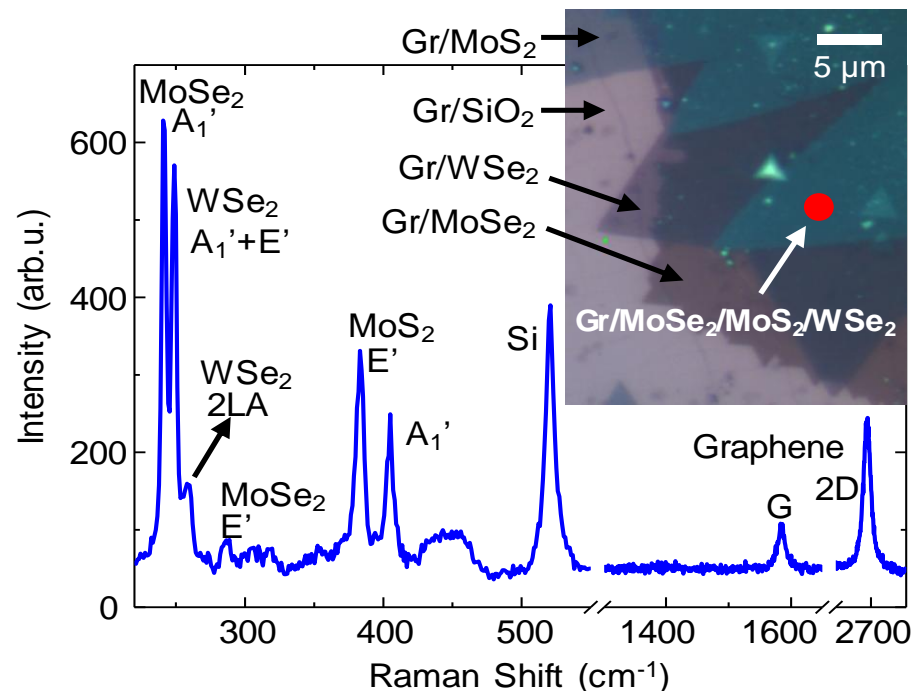
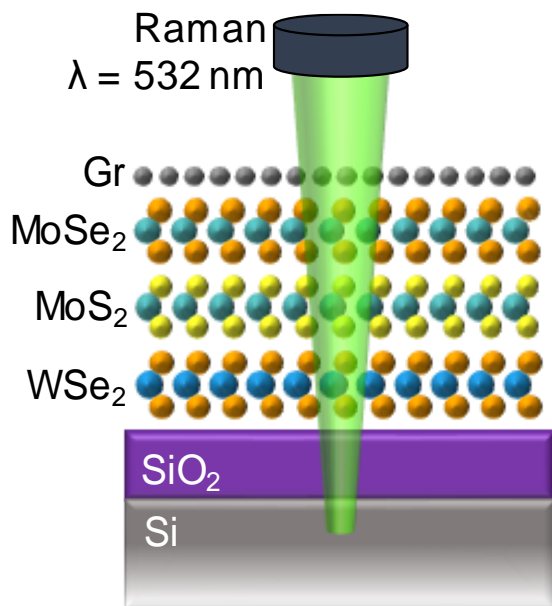
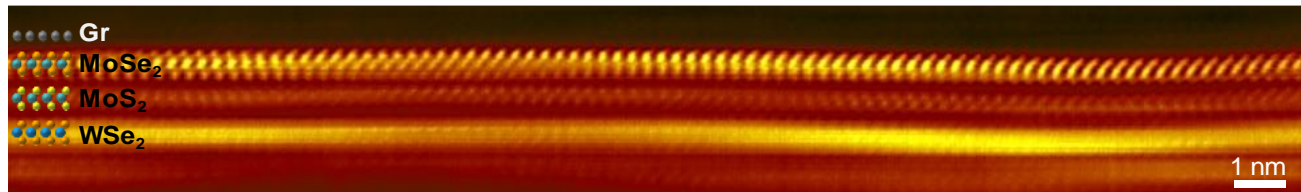
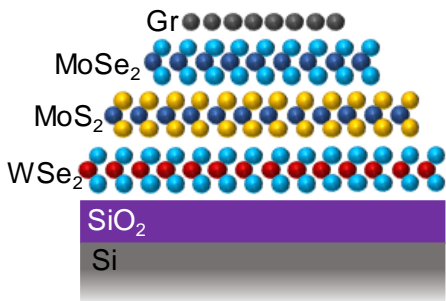
Example



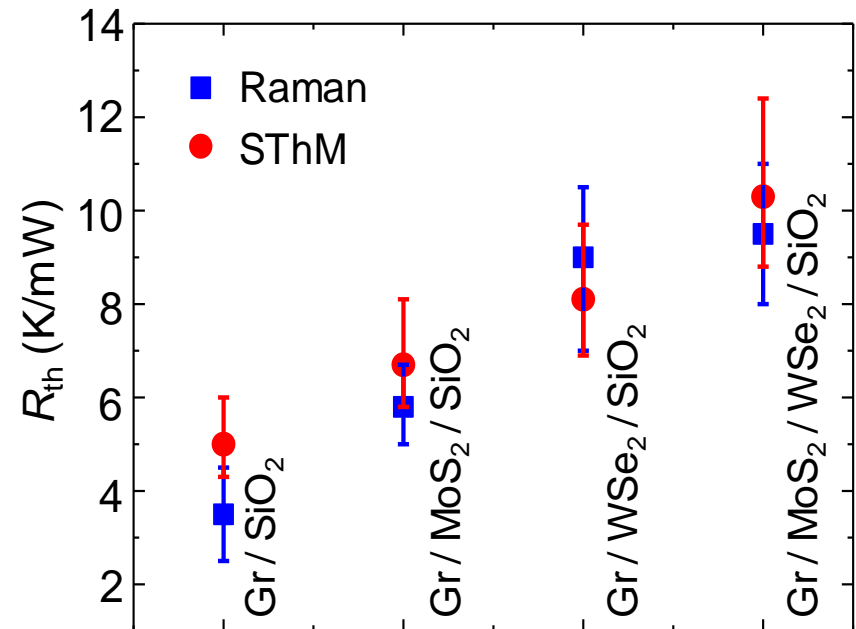
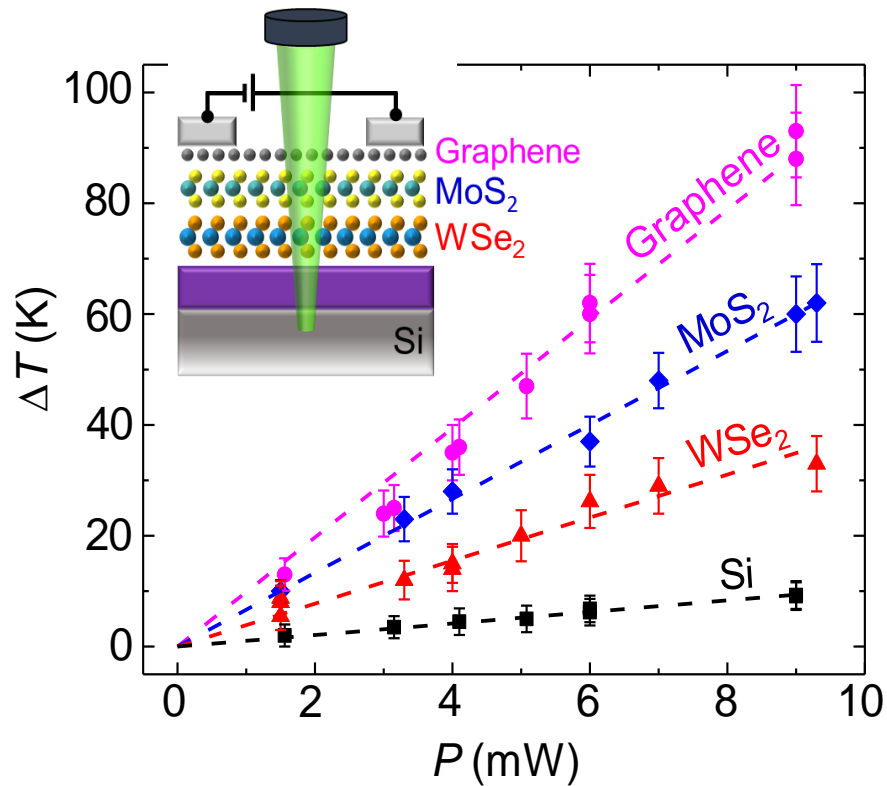
Kimling et al., *Phys. Rev. B*, 91, 144405 (2015)

# Ultra-thin thermal barriers

- Need for ultra-thin and high thermal resistive barriers
- Routing heat to desired locations



# Thermal barriers based on 2D heterostructures

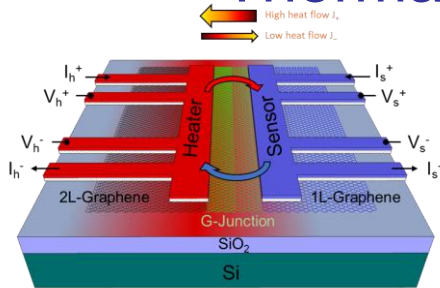


- Stack thickness  $\sim 3$  nm with clean, residue free interfaces
- Artificial stack (Gr-MoS<sub>2</sub>-WSe<sub>2</sub>) possess a thermal resistance equivalent to 300nm SiO<sub>2</sub>
- Thermal barriers for thermal routing applications

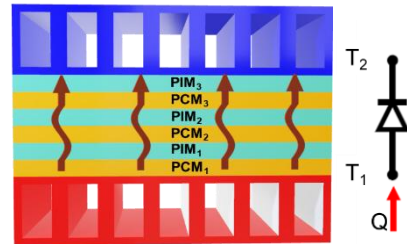
S. Vaziri\*, E. Yalon\*, **M. Muñoz Rojo** *et al*, *Science Advances*, 2019

# Non Linear Thermal Control Devices

## Thermal diodes

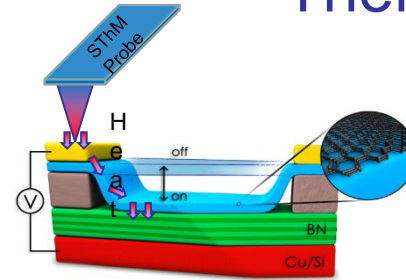


M. Muñoz Rojo *et al*, *2D Materials*, 6, (1) 2018



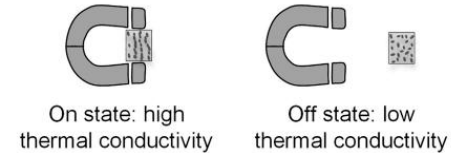
T. Swoboda, K. Klinar, S. Abbasi, G. Brem, A. Kitanovsky, & M. Muñoz Rojo, *iScience*, 24, (2021)

## Thermal switches



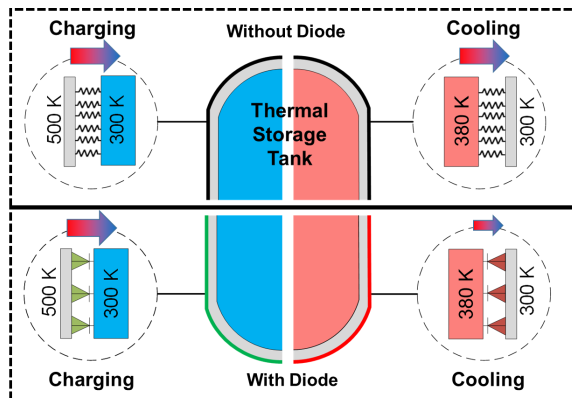
M. Chen, M. Muñoz Rojo, F. Lian and E. Pop. *2D materials*, 8, (3) (2022)

### Ferrofluidic thermal switch



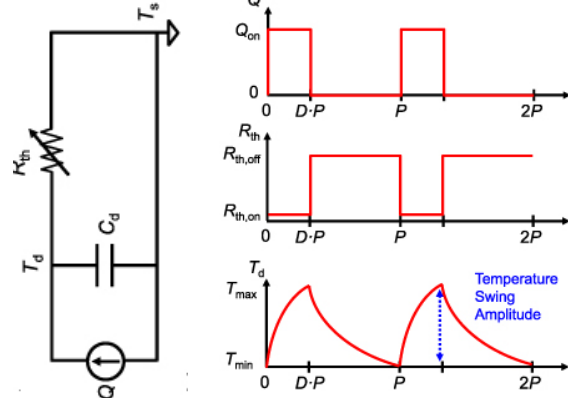
K. Klinar, T. Swoboda, M. Muñoz Rojo and A. Kitanovski, *iScience* 25, (2022)

Applied to heat batteries, thermal management of electronics or magnetocaloric refrigeration:



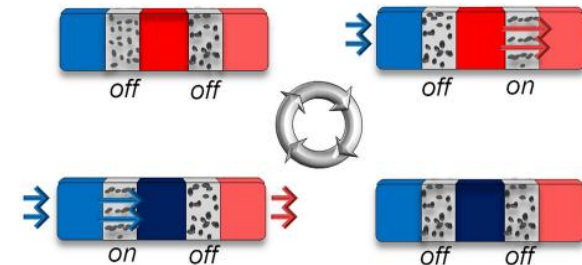
Thermal Resistor, Diode forward bias, Diode reverse bias

T. Swoboda, K. Klinar, S. Abbasi, G. Brem, A. Kitanovsky, & M. Muñoz Rojo, *iScience*, 24, (2021)



M. Chen, M. Muñoz Rojo, F. Lian and E. Pop. *2D materials*, 8, (3) (2022)

### Ferrofluidic thermal switches in a magnetocaloric device



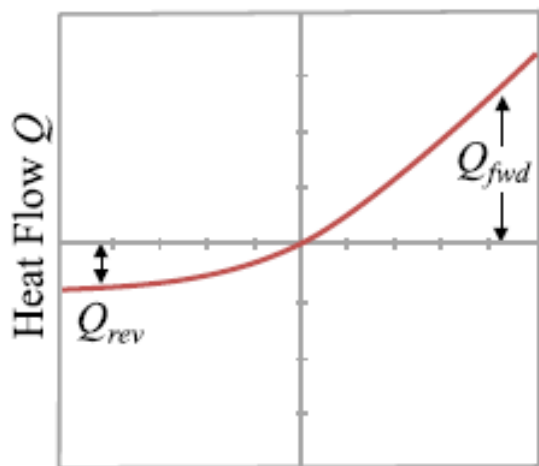
K. Klinar, T. Swoboda, M. Muñoz Rojo and A. Kitanovski, *iScience* 25, (2022)

# Thermal Rectification

## Diode



Transfer Function:  
Asymmetric

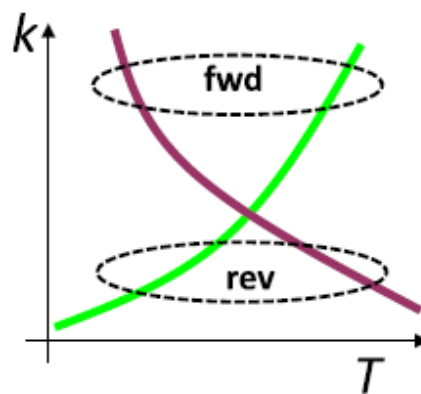


Thermal Bias  $\Delta T = T_1 - T_2$   
( $T_{avg}$  fixed)

$$RR = \frac{Q_{fwd} - Q_{rev}}{Q_{rev}}$$

## Examples

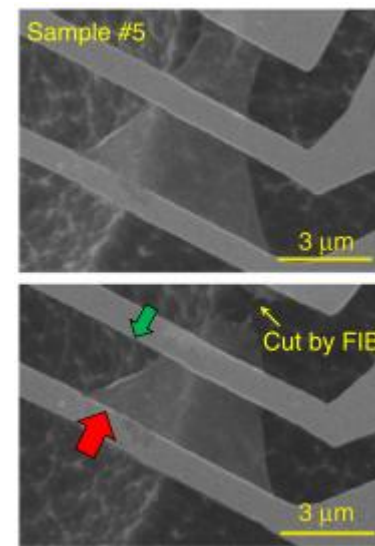
Junction of Materials  
with Different Thermal  
Properties (JMT)



$RR \sim 70 \%$

Low temperatures

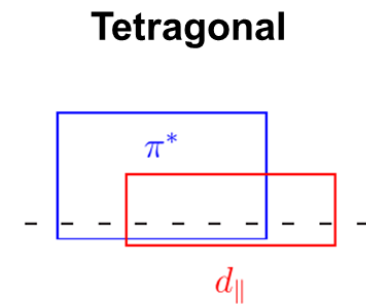
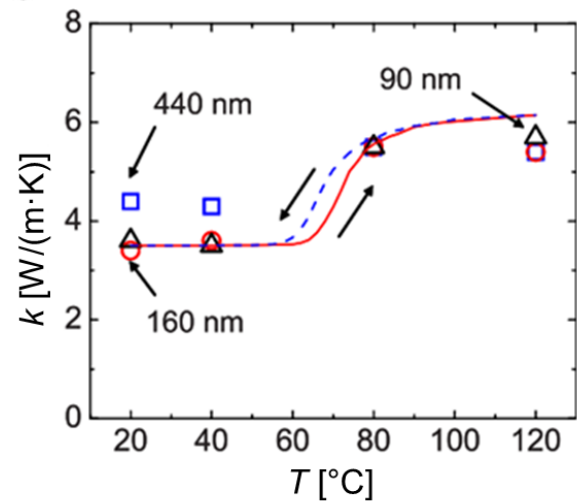
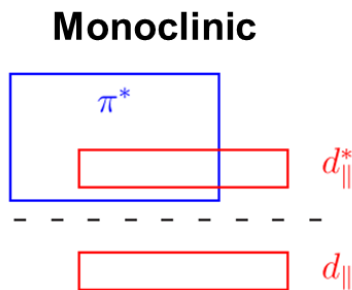
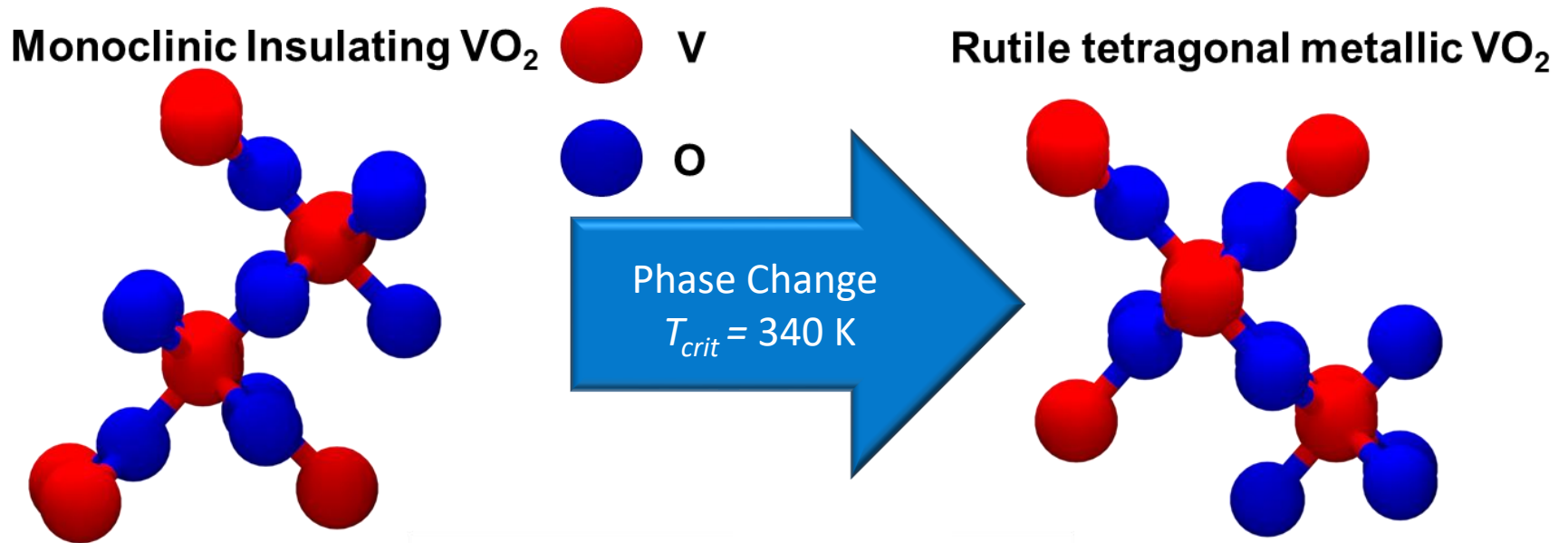
Shape-Induced  
Thermal Diodes (SID)



$RR \sim 11 \%$

Low RR

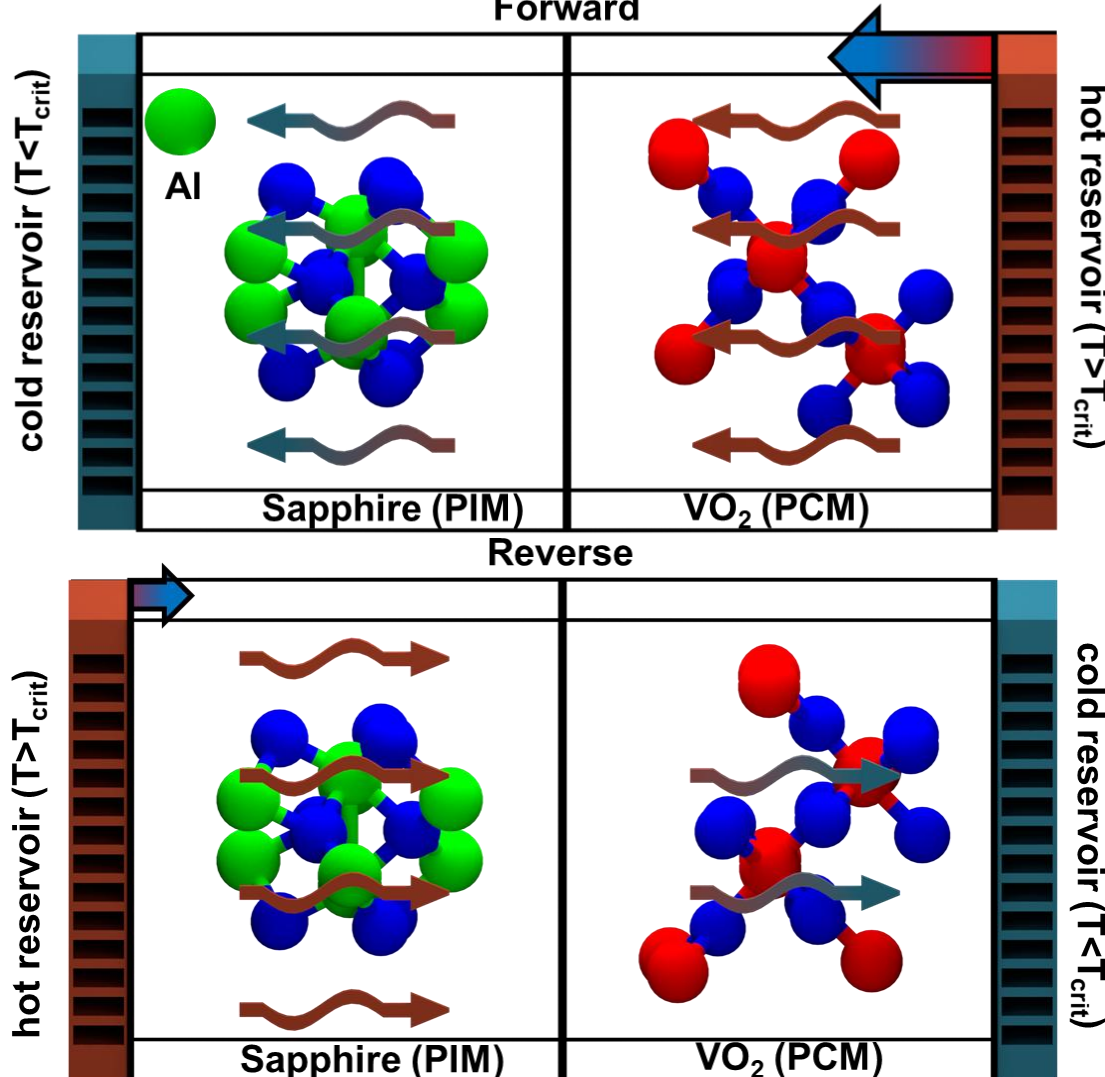
# Phase change materials



Swoboda *et al.* *Adv. Electron. Mater.* **7**, 2000624 (2020)

# PCM thermal diodes

Phase change (PCM) and invariant (PIM) diodes



$$T(VO_2) > T_{crit}(VO_2)$$

$$k(VO_2) \rightarrow \text{high}$$

$$T(VO_2) < T_{crit}(VO_2)$$

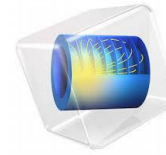
$$k(VO_2) \rightarrow \text{low}$$

$$Q_{fwd} > Q_{rev}$$

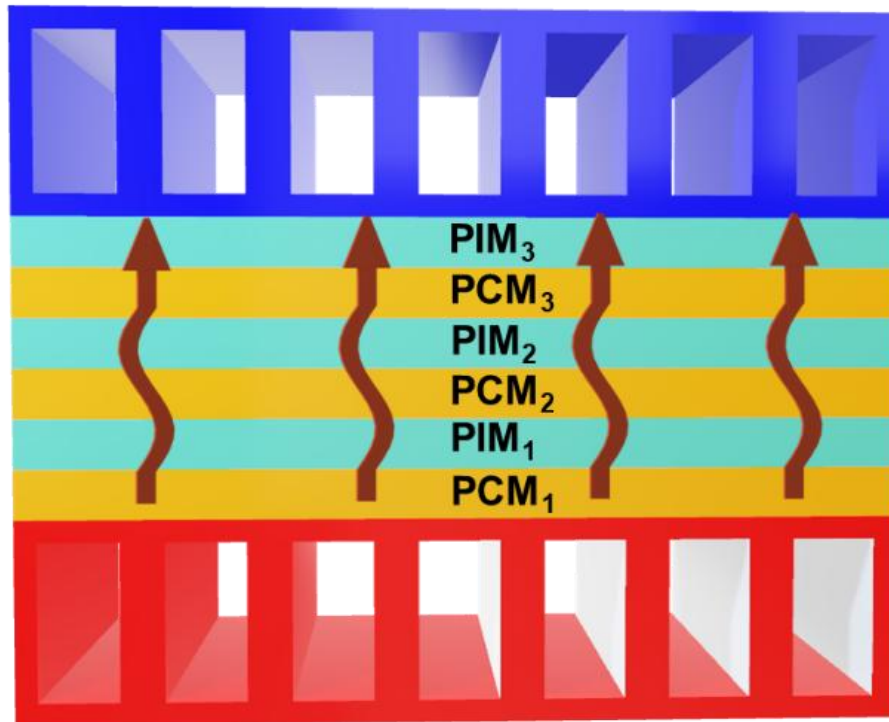
Swoboda *et al.* *Adv. Electron. Mater.* **7**, 2000624 (2020)

# Multiple PCM/PIM diode design

- $T_{source} = 500 \text{ K}$ ;  $T_{sink} = 300 \text{ K}$

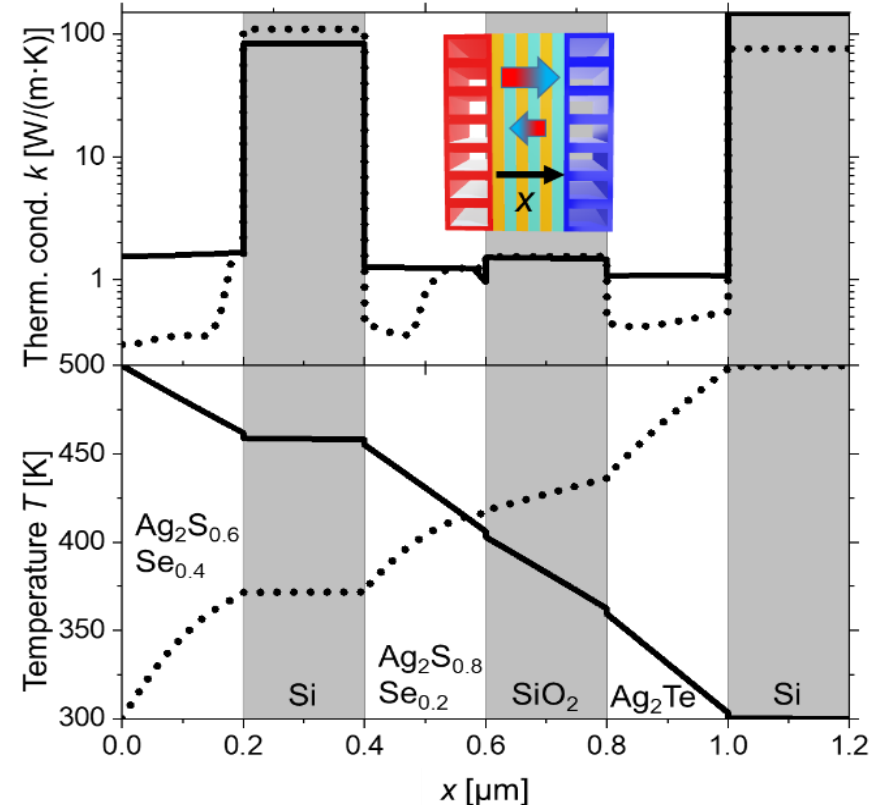


Finite Element Modelling (FEM)



PIM Layers

PCM Layers



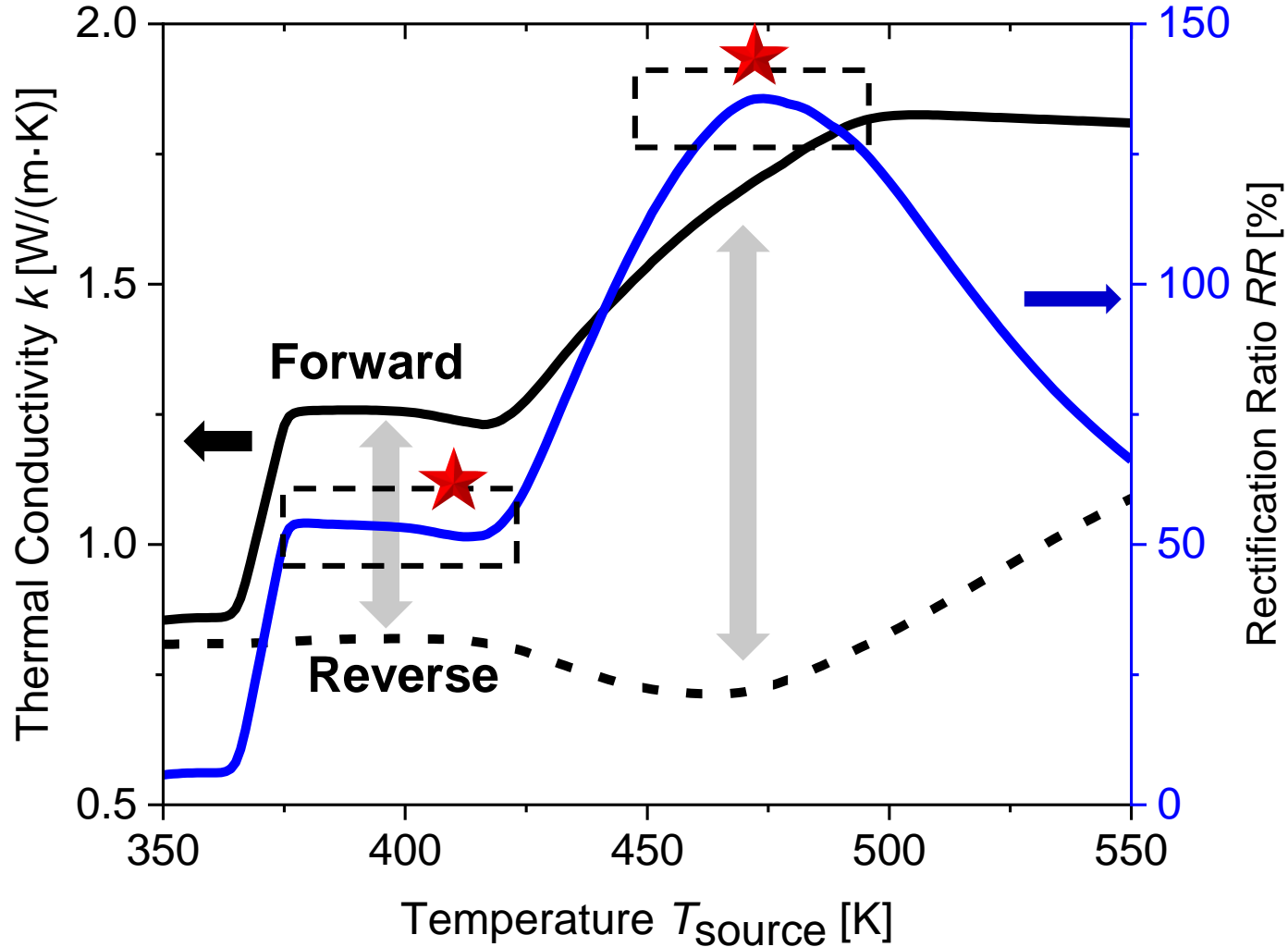
Solid Line: Forward; Dotted Line: Reverse

Max  $RR = 119 \%$

$$RR = \frac{Q_{fwd} - Q_{rev}}{Q_{rev}}$$

Swoboda *et al.* *iScience*, **24**, 102843 (2021)

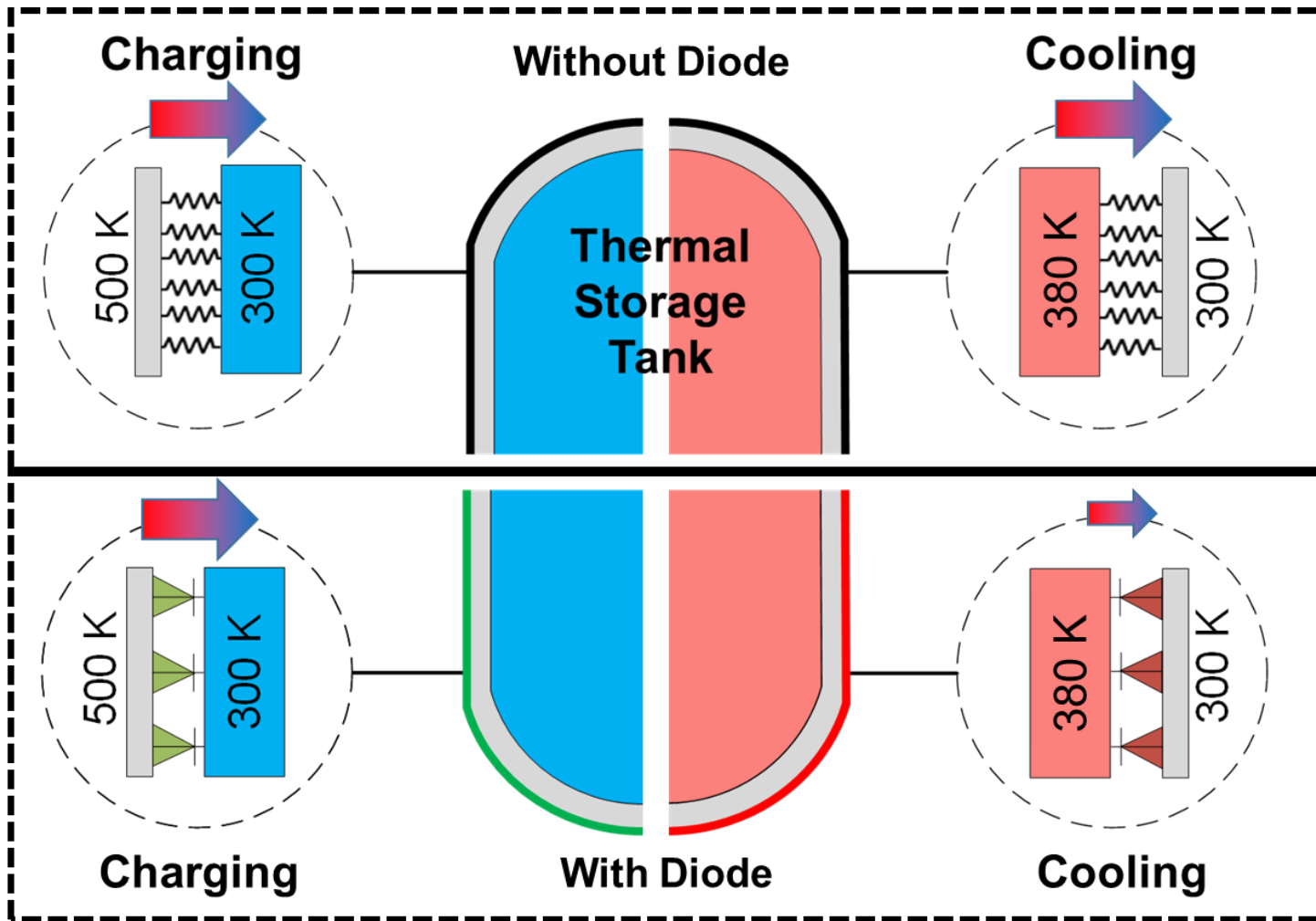
# 3 PCM Thermal Rectification vs Temperature



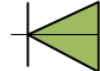
- High Rectification Ratio – max 136 %
- Temperature modulation

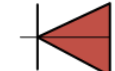
$$RR = \frac{Q_{fwd} - Q_{rev}}{Q_{rev}}$$

# Thermal diodes for energy storage



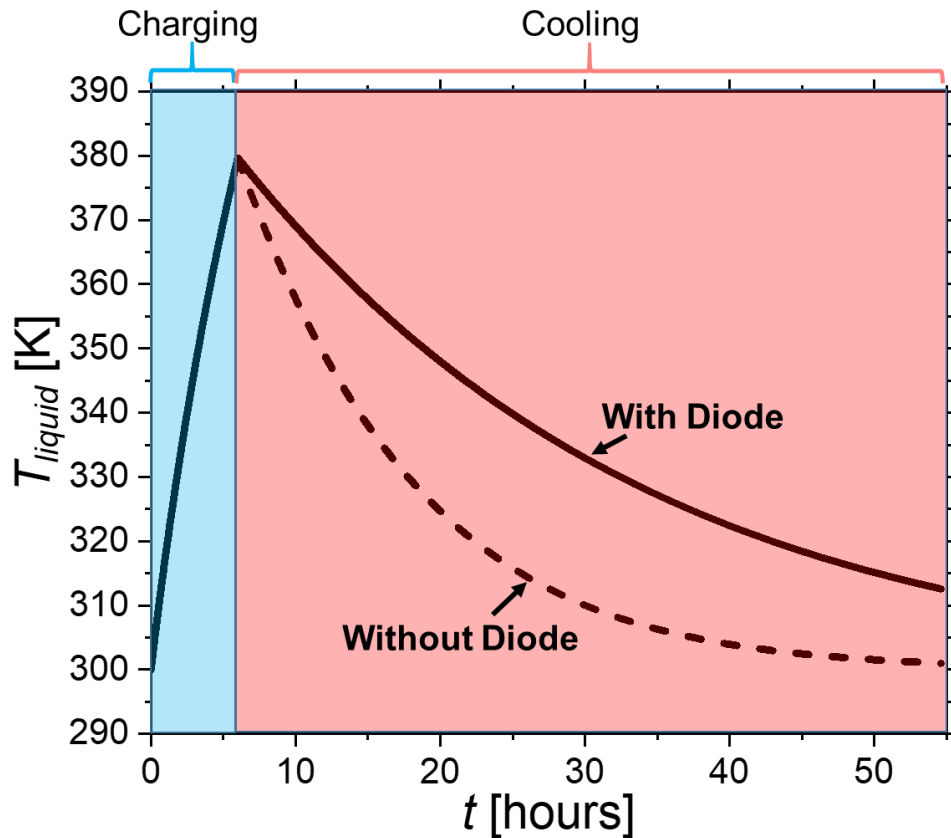
 Thermal Resistor

 Diode forward bias

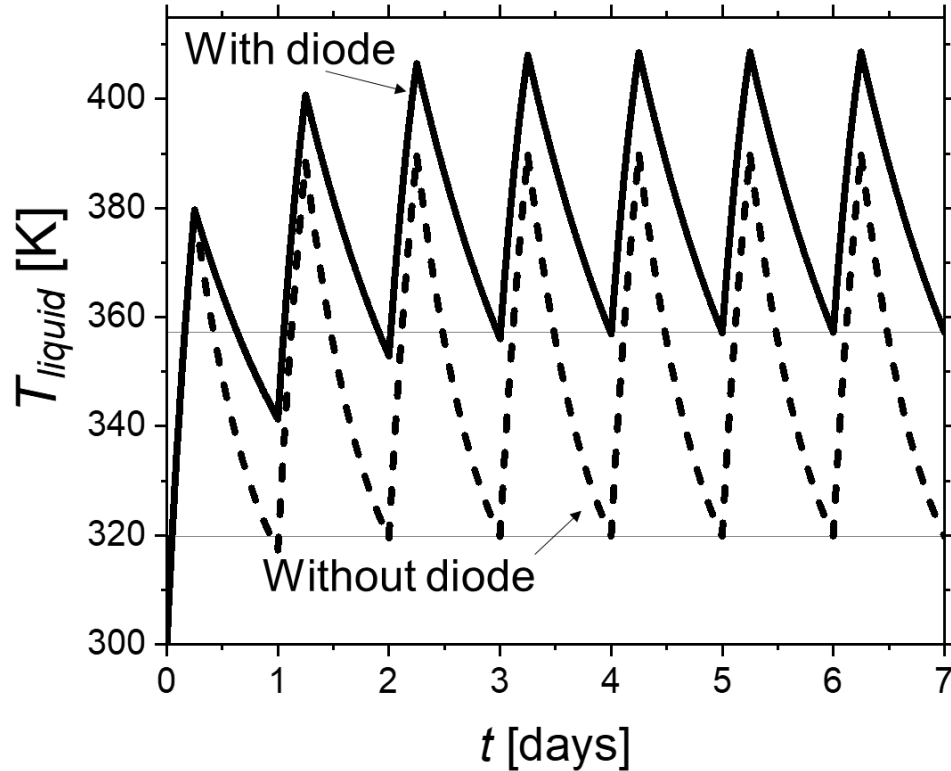
 Diode reverse bias

Swoboda *et al.* *iScience*, **24**, 102843 (2021)

# Heat Retention



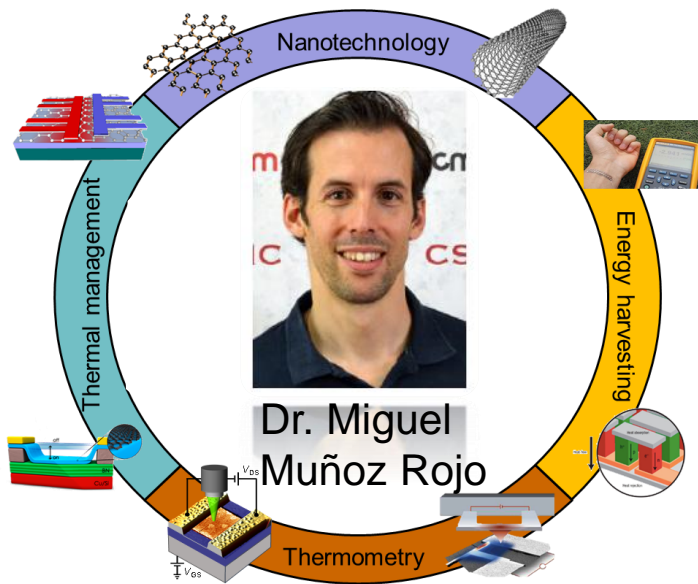
**Cooling to original state**



**7 – Day cycle**

- Diode configuration is able to retain more energy

# Thank you for your attention!



Dr. Miguel  
Muñoz Rojo

m.m.rojo@csic.es

## Postdoc



Dr. Xinming Xing  
Proj. manager



Salustiano Torre

## PhD students



Rem Elnahas



Elvira Tornero



Kutay Ozyurt



Azra Khan



Wenkang Chen



Mauro Ramos



PID2023-149764OA-I00



ERC CoG 2024-2029



NL Science  
Foundation

THALES



InnoEnergy

Industrial partners

## Selected publications:

- M. Muñoz Rojo, et al., **Science Advances**, 8, 13, 2022
- M. Muñoz Rojo, **Adv. Funct. Mat.**, 30, 18, 2020
- K. Zhu, [..], M. Muñoz Rojo, et al., **Nature**, 618, 57-62, 2023
- S. Bohaichuk, M. Muñoz Rojo, **ACS Nano**, 13, 10, 2019
- I. Datye, M. Muñoz Rojo, et al., **Nano Letters**, 20, 2, 2020
- E. Yalon, S. Deshmukh, M. Muñoz Rojo, et al. **Sci.Rep.**, 2017